Unit in mm

TOSHIBA Diode Silicon Epitaxial Planar Type

HN2D01FU

Ultra High Speed Switching Application

- HN2D01FU is composed of 3 independent diodes.
- Low forward voltage $: V_{F(3)} = 0.98V$ (typ.)
- Fast reverse recovery time: t_{rr} = 1.6ns (typ.)
- Small total capacitance $: C_T = 0.5 pF (typ.)$

Pin Assignment (Top View)





Marking

Maximum Ratings (Ta = 25°C)

| Characteristic | Symbol | Rating | Unit |
|--------------------------------|------------------|---------|------|
| Maximum (peak) reverse Voltage | V _{RM} | 85 | V |
| Reverse voltage | VR | 80 | V |
| Maximum (peak) forward current | I _{FM} | 240 * | mA |
| Average forward current | Ι _Ο | 80 * | mA |
| Surge current (10ms) | I _{FSM} | 1 * | A |
| Power dissipation | Р | 200 | mW |
| Junction temperature | Тј | 125 | °C |
| Storage temperature | T _{stg} | -55~125 | °C |



Weight: 6.2mg

: This is maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 ro 3 diodes, the maximum ratings per diodes is 75 % of the single diode one.

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Electrical Characteristics (Q1 Q2 Q3 Common, Ta = 25°C)

| Characteristic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|-----------------------|--------------------|-----------------|--|-----|------|------|------|
| Forward voltage | V _{F (1)} | - | I _F = 1mA | _ | 0.62 | - | |
| | V _{F (2)} | _ | I _F = 10mA | | 0.75 | _ | V |
| | V _{F (3)} | - | I _F = 100mA | - | 0.98 | 1.20 | |
| Reverse current | I _{R (1)} | _ | V _R = 30V | _ | — | 0.1 | μA |
| | I _{R (2)} | - | V _R = 80V | | _ | 0.5 | |
| Total capacitance | CT | — | V _R = 0, f = 1MH _z | | 0.5 | 3.0 | pF |
| Reverse recovery time | t _{rr} | — | I _F = 10mA (Fig.1) | | 1.6 | 4.0 | ns |

Fig.1 Reverse Recovery Time (trr) Test Circuit



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Q1, Q2, Q3 Common



Q1, Q2, Q3 Common



Q1, Q2, Q3 Common

